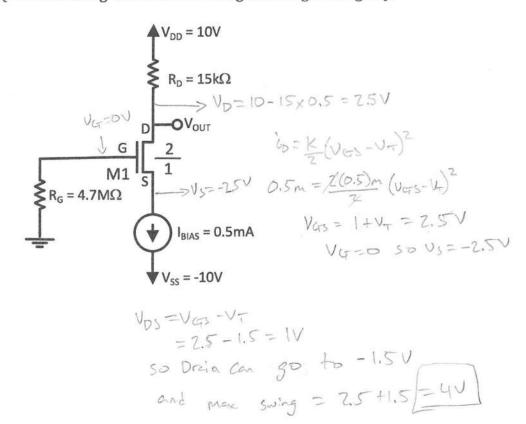
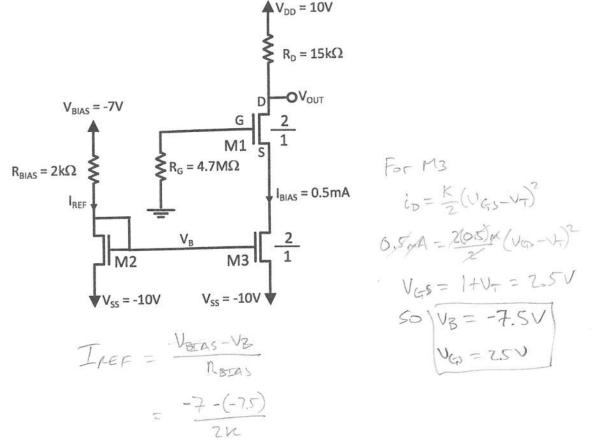
15pts

- 1) The circuit below is biased using a constant current source to set I_{DS} for the MOSFET. $V_T = 1.5V$ and $K_n' = 0.5 \text{mA/V}^2$, and remember $K_n = (W/L) K_n'$.
 - a) Find all of the DC node voltages: V_D , V_S , V_G , and V_{GS} .
 - b) What is the maximum swing at the drain for which the MOSFET remains in saturation (without taking into account the signal swing at the gate)?



- 2) Now complete the design of the current mirror in the circuit below to provide the bias current of 0.5mA for the circuit of problem 1.
 - a) What is the voltage at V_B , and what is V_{GS} for M2 and M3?
 - b) What is W/L for M2?



$$I_{FEF} = \frac{V_{BTAS} - V_{B}}{R_{BTAS}}$$

$$= \frac{-7 - (-7.5)}{2K}$$

$$= \frac{6.5}{2K} = 0.25 \text{ mA}$$

For M3

$$i_D = \frac{K}{2}(v_{GS} - v_T)^2$$

 $0.5_{pA} = \frac{2(0.5)m}{2}(v_{GS} - v_T)^2$
 $V_{GS} = 1 + v_T = 2.5 V$
 $V_{GS} = -7.5 V$
 $v_{GS} = 2.5 V$

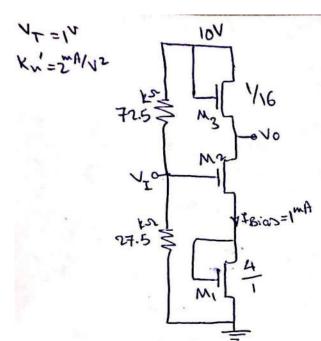
For M2
$$i_0 = \frac{1}{2}(v_{45} - v_{7})^{2}$$
 $0.25 = \frac{1}{2}(v_{45} - v_{7})^{2}$
 $V = 0.5 \Rightarrow \frac{1}{2} = \frac{1}{2}$

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 $\frac{\sqrt{9} + \sqrt{10}}{\sqrt{10}} = -\frac{1}{9} \times (\sqrt{10} - \sqrt{10}) \times \sqrt{10}$ $= -\frac{1}{10} (1.6 - 1)$ $\frac{\sqrt{10} + \sqrt{10}}{\sqrt{10}} = -\frac{1}{10} \times \sqrt{10}$ $\frac{\sqrt{10} + \sqrt{10}}{\sqrt{10}} = -\frac{1}{1$ Voutz (1+gmlz) = gmzRz = 1 Voutz = gmzRz = 1+1gmzRz

$$\begin{array}{c}
(72 = \frac{1}{1 + \sqrt{g_{m2}(\Omega_2 || \Omega_0 A0)}} \\
= \frac{1}{1 + \sqrt{g_{m3}}} = 0.79
\end{array}$$

- f) The overell gain of the 2 stage comp is
 higher when driving RLOAD COMPared to
 higher when driving RLOAD COMPared to
 if the first common source star directly
 drives RLOAD (1.6x) which shows the second
 drives RLOAD (1.6x) which shows the second
 stage is functioning as a voltage before.
 - (9) gm and gm correspond to the opening point
 from problem #2.



Note: For M. & M3, because their Gate and Drain are Connected, they will be in Saturation region because:

a)
$$V_{I} = \frac{27.5^{k22}}{27.5^{k22} + 72.5^{k22}} \times 10^{5} = 2.75^{5}$$

Therein equivalent: RH = 27.5 kg x72.5 = 20

For M3: $i_D = \frac{k}{2}(V_{GS_3} - V_1)^2$ $i_D = \frac{k}{2}(V_{GS_3} - V_1)^2$ $i_D = \frac{2}{16x^2}(V_{GS_3} - V_1)^2$

For M1: $i_0 = \frac{k}{2} (V_{GSI} - V_T)^2$ $v_{M} = \frac{4(2^{N}V^2)}{2} (V_{GSI} - 1)^2$ $V_{GSI} = \frac{1}{2} + \frac{1}{2} \cdot \frac{1}{5} \cdot \frac{1}{$

For M2: VGs2=V5-VG1=2.75-1.5=1.2571 VDS=V0-VG1=5-1.5=3.570.25V

Mz is in saturation:

$$io = k_{12}(V_{GS} - V_{T})^{2}$$
 $I^{mA} = k_{12}(V_{GS} - V_{T})^{2} = k_{12}(V_{4})^{2}$
 $k = 32^{m} = \frac{W}{L}(2^{m}N_{1}V_{2})$
 $= D[W]_{L} = \frac{16}{1}$

now use this model in the circuit's small signal model &

$$g_{m} = \frac{2TD}{VGS-VT} = K(VGS-VT) + DS = \frac{2TD}{VGS-VT} = \frac{2TD}{VGS-VT$$